N-Channel Enhancement Mode MOSFET

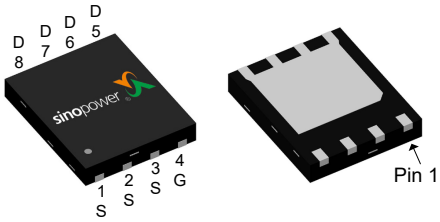
Features

- 100V/100A*
  $R_{DS(ON)}$=3.4mΩ(max.)@V_{GS}=10V
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

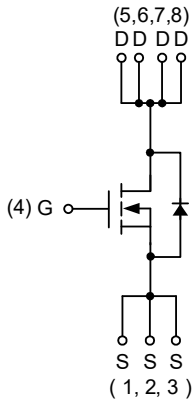
Applications

- High Efficiency Synchronous Rectification in SMPS.
- Uninterruptible Power Supply.
- Hard Switched and High Frequency Circuits.

Pin Description



DFN5x6O-8_EP



N-Channel MOSFET

Ordering and Marking Information

SM1A90NH □□□-□□ □ Assembly Material Handling Code Temperature Range Package Code	Package Code QG : DFN5x6O-8_EP Operating Junction Temperature Range D : -55 to 175 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
SM1A90NH QG : 1A90NH XXXXX	XXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines “Green” to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		175	°C
T_{STG}	Storage Temperature Range		-55 to 175	
I_S	Diode Continuous Forward Current	T_C=25°C	94	A
I_D	Continuous Drain Current	T_C=25°C	100*	A
		T_C=100°C	100*	
I_{DM}[a]	Pulsed Drain Current	T_C=25°C	400*	
P_D	Maximum Power Dissipation	T_C=25°C	300	W
		T_C=100°C	150	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		0.5	°C/W
I_D	Continuous Drain Current	T_A=25°C	18	A
		T_A=70°C	15	
P_D	Maximum Power Dissipation	T_A=25°C	2.7	W
		T_A=70°C	1.9	
$R_{\theta JA}$[c]	Thermal Resistance-Junction to Ambient		55	°C/W
I_{AS}[b]	Avalanche Current, Single pulse	L=0.5mH	46	A
E_{AS}[b]	Avalanche Energy, Single pulse	L=0.5mH	529	mJ

Note * : Current limited by bonding wire.
Note a : Pulse width limited by maximum junction temperature.
Note b : UIS tested and pulse width limited by maximum junction temperature (initial temperature T_j=25°C).
Note c : Surface mounted on 1in^2 pad area.

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Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V, V_{GS}=0V	-	-	1	μA
		T_J=85°C	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	2	3	4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$ [d]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=50A	-	2.8	3.4	mΩ
Diode Characteristics						
V_{SD} [d]	Diode Forward Voltage	I_{SD}=45A, V_{GS}=0V	-	0.8	1.1	V
t_{rr}	Reverse Recovery Time	I_{SD}=50A, dI_{SD}/dt=100A/μs	-	65	-	ns
Q_{rr}	Reverse Recovery Charge		-	147	-	nC
Dynamic Characteristics [e]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz	-	1.5	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=50V, Frequency=1.0MHz	-	5540	7200	pF
C_{oss}	Output Capacitance		-	750	-	
C_{rss}	Reverse Transfer Capacitance		-	92	-	
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=30V, R_L=30Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω	-	32	58	ns
t_r	Turn-on Rise Time		-	28	50	
$t_{d(OFF)}$	Turn-off Delay Time		-	98	176	
t_f	Turn-off Fall Time		-	156	281	
Gate Charge Characteristics [e]						
Q_g	Total Gate Charge	V_{DS}=50V, V_{GS}=10V, I_{DS}=50A	-	110	165	nC
Q_{gs}	Gate-Source Charge		-	24	-	
Q_{gd}	Gate-Drain Charge		-	36	-	

Note d : Pulse test ; pulse width≤300μs, duty cycle≤2%.
Note e : Guaranteed by design, not subject to production testing.

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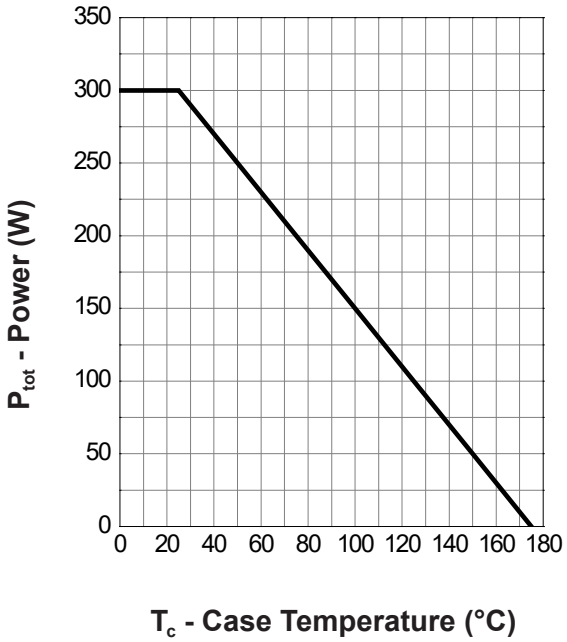
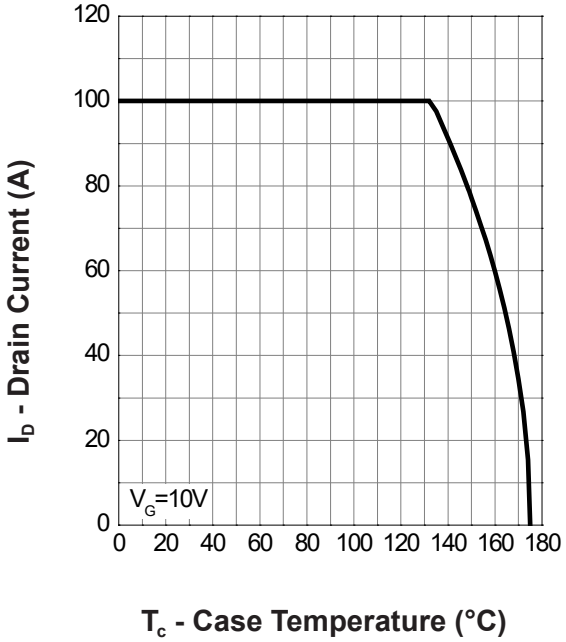
Typical Operating Characteristics

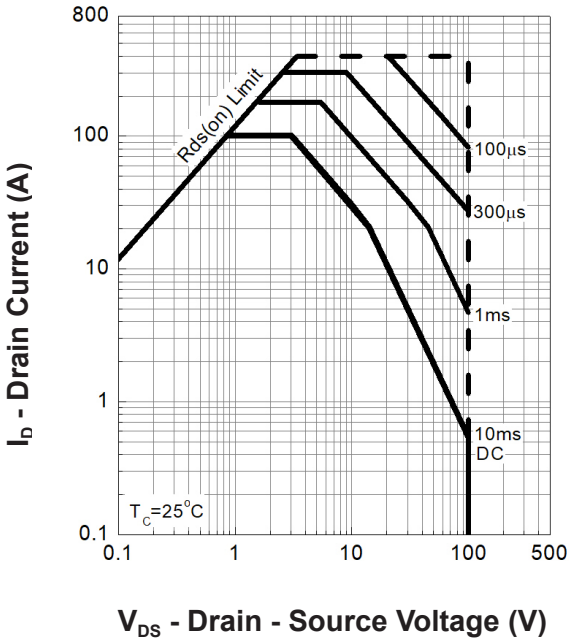
Power Dissipation



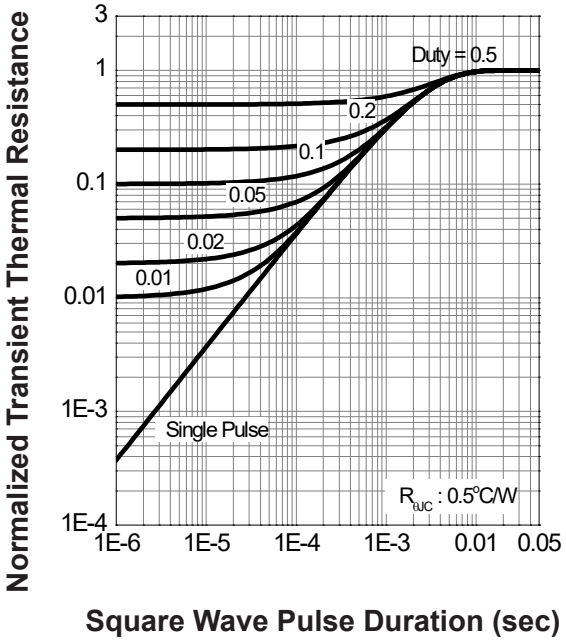
Drain Current



Safe Operation Area

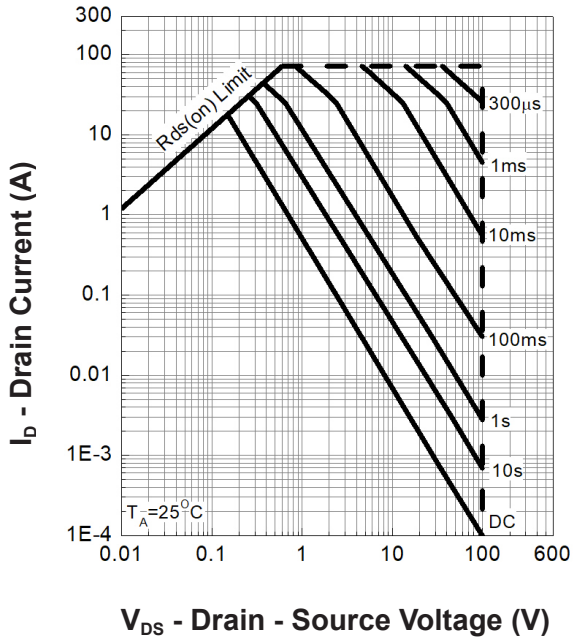


Thermal Transient Impedance

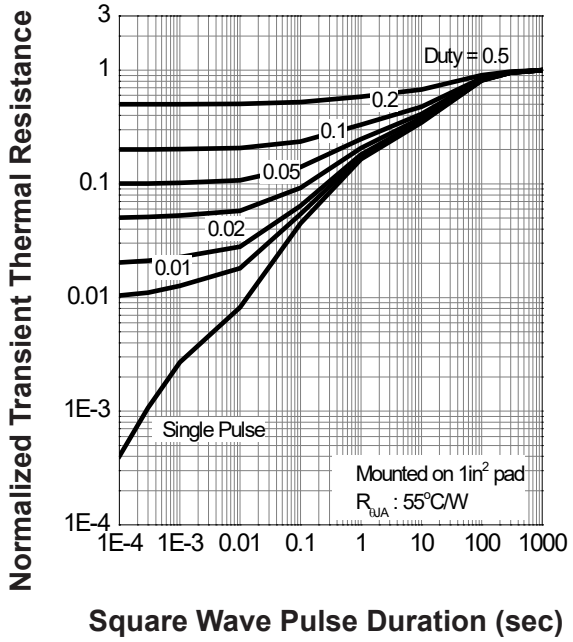


Typical Operating Characteristics(Cont.)

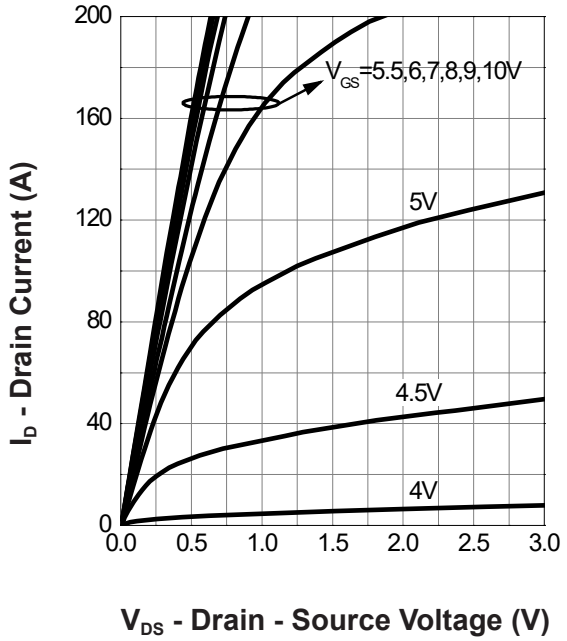
Safe Operation Area



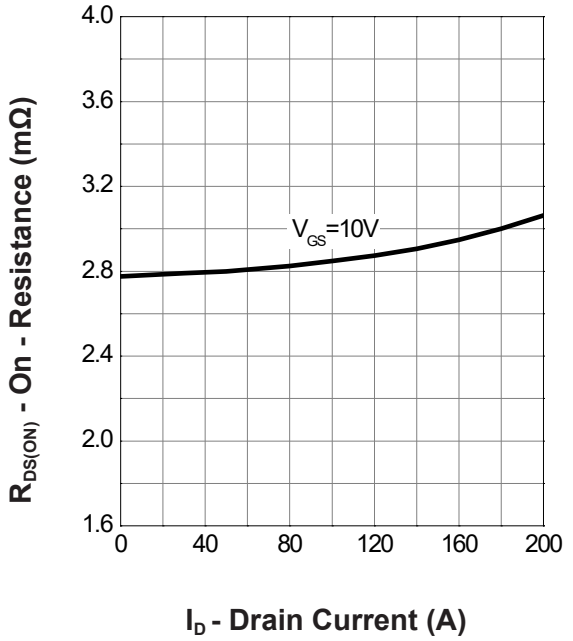
Thermal Transient Impedance



Output Characteristics



Drain-Source On Resistance



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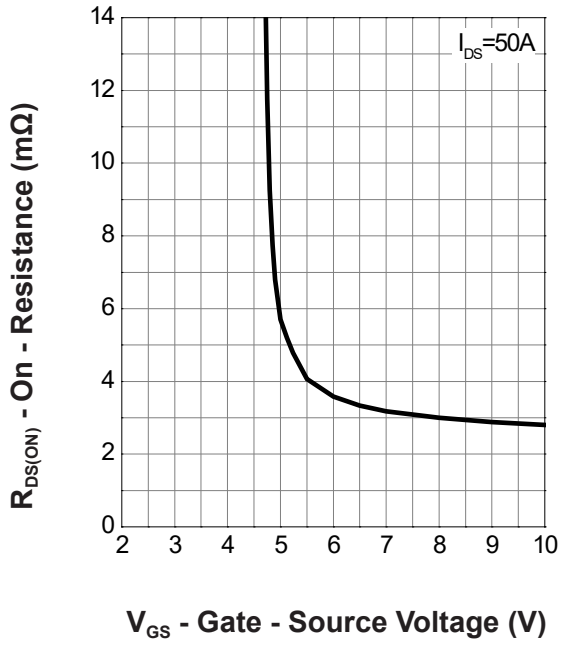
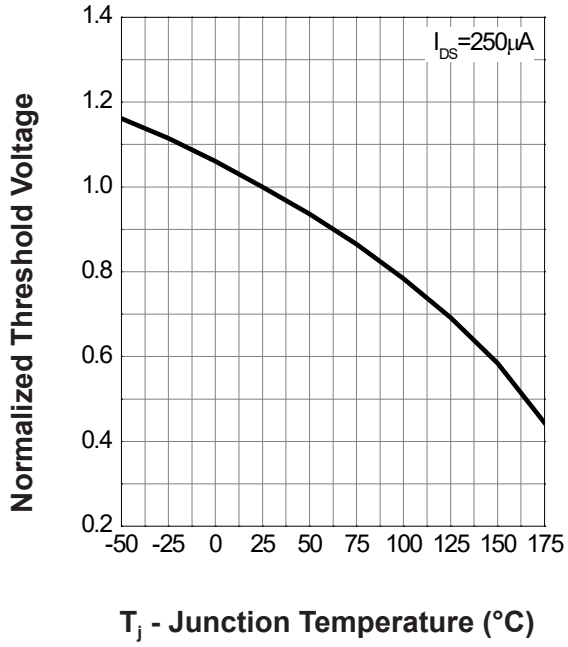
Typical Operating Characteristics(Cont.)

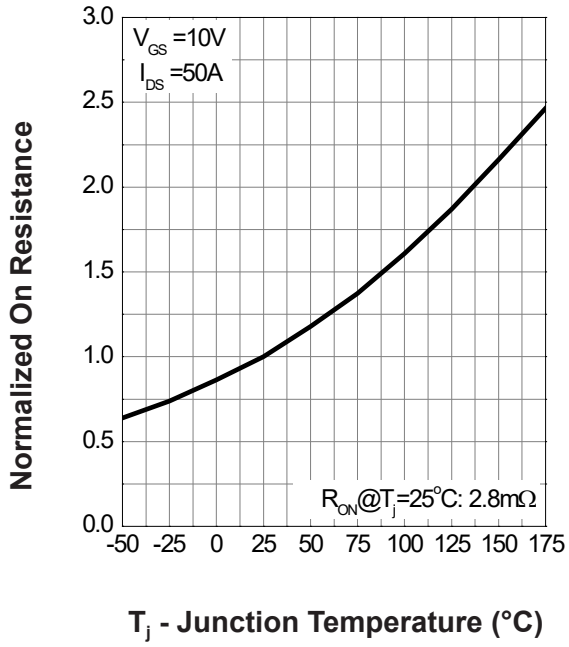
Gate-Source On Resistance



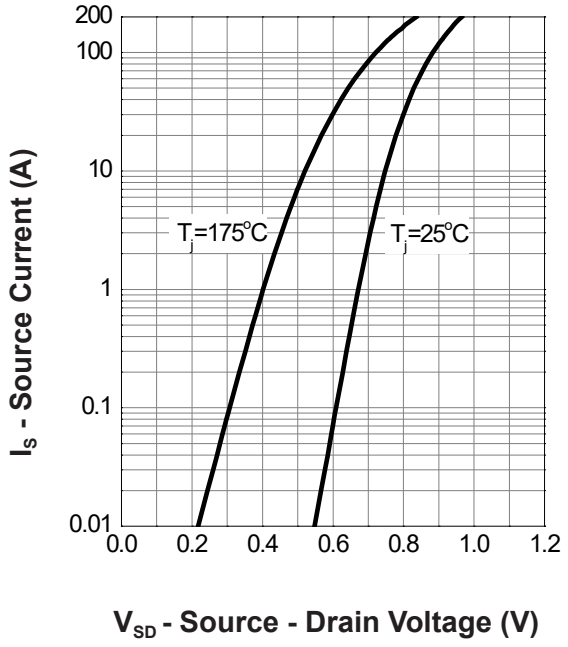
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward



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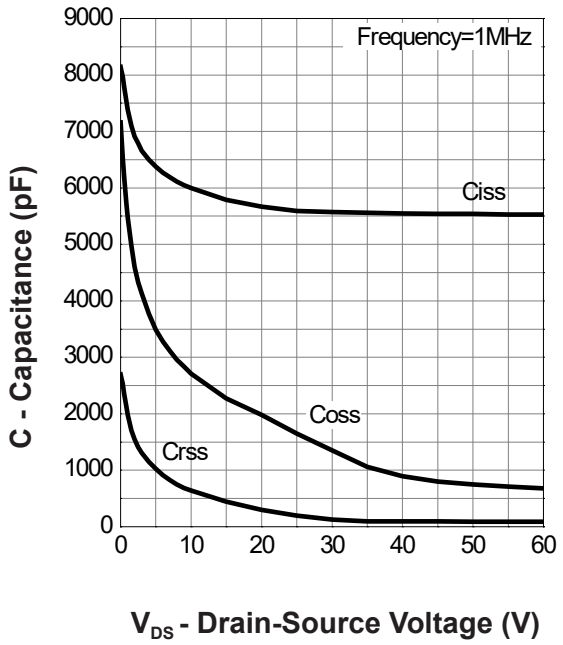
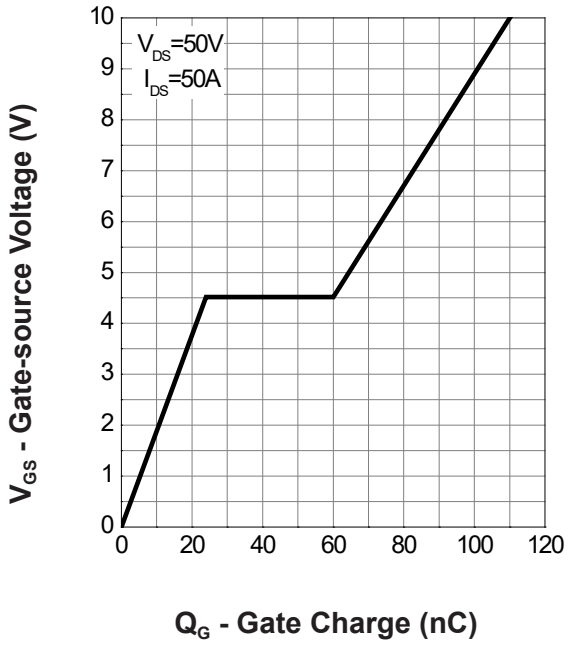
Typical Operating Characteristics(Cont.)

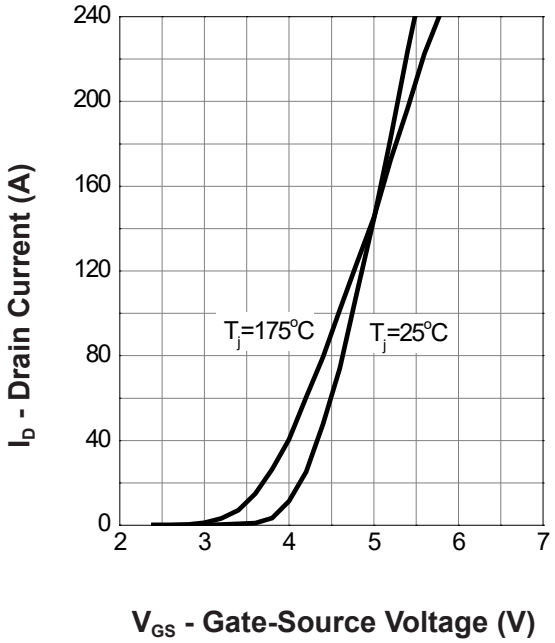
Capacitance



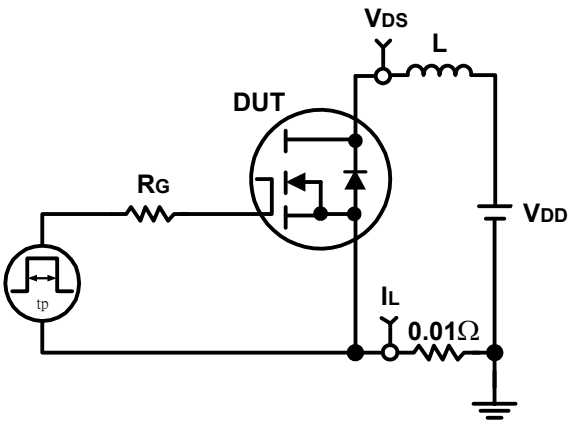
Gate Charge

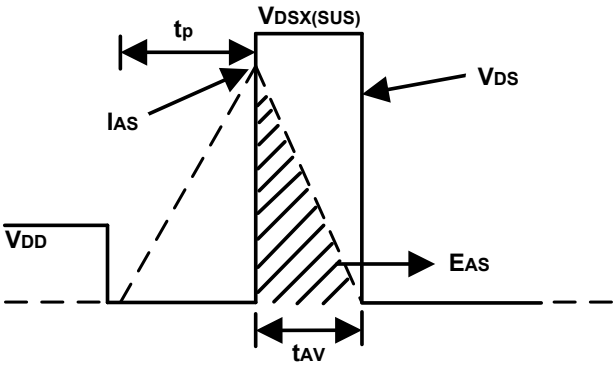


Transfer Characteristics

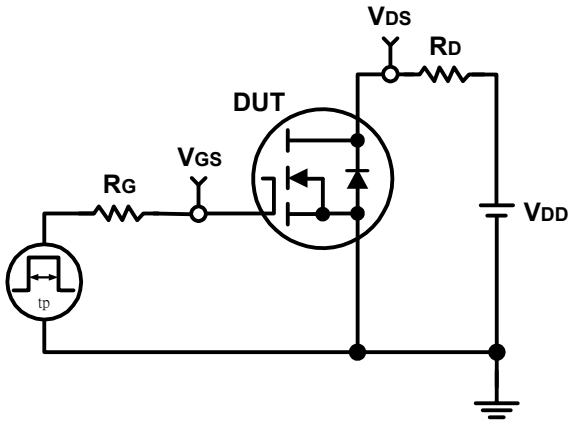


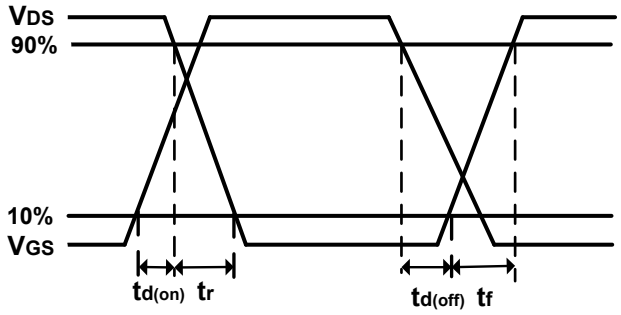
Avalanche Test Circuit and Waveforms





Switching Time Test Circuit and Waveforms





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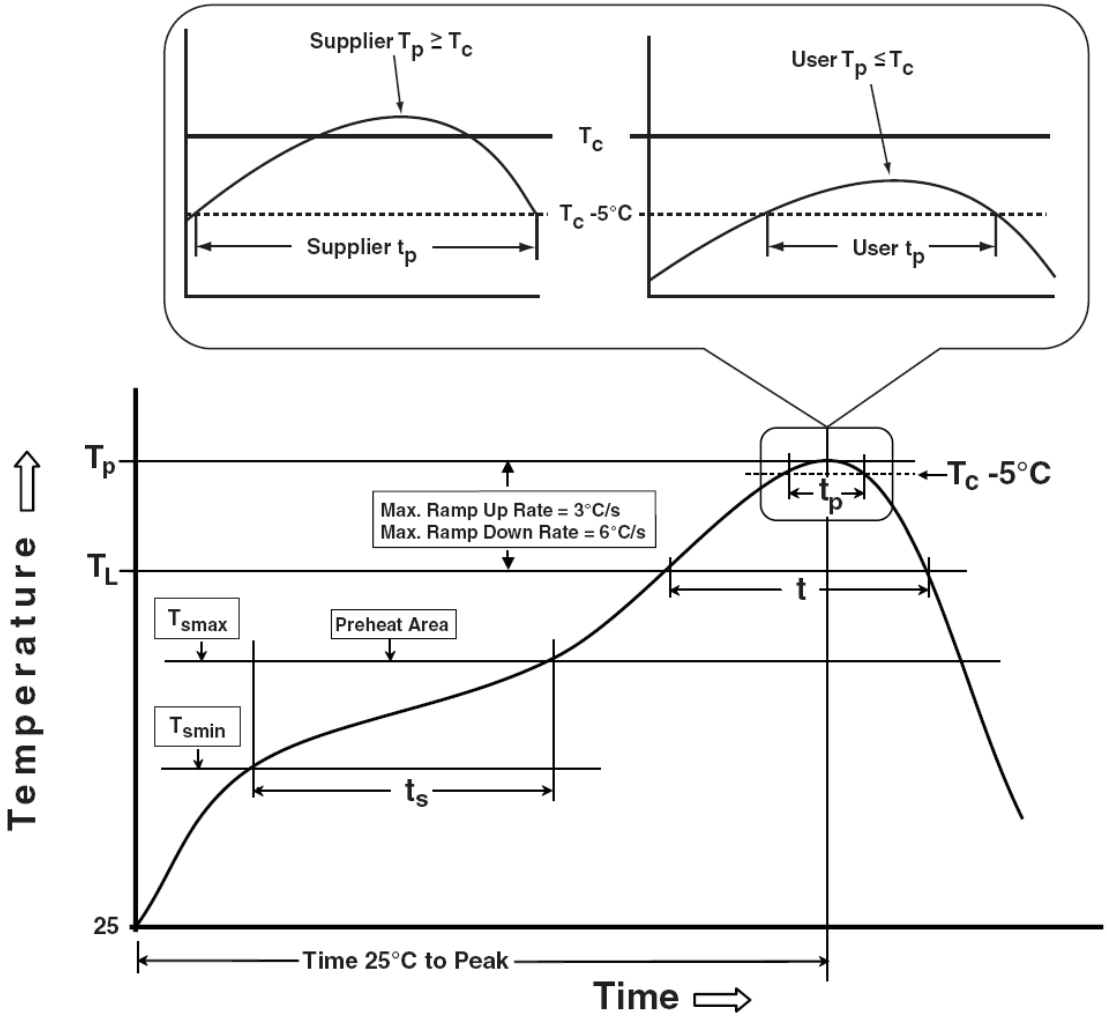
Classification Profile



Classification Reflow Profiles

Profile Feature	**Sn-Pb Eutectic Assembly**	**Pb-Free Assembly**
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	**Volume mm^3 <350**	**Volume mm^3 ≥350**
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	**Volume mm^3 <350**	**Volume mm^3 350-2000**	**Volume mm^3 >2000**
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Customer Service

Sinopower Semiconductor Inc.

5F, No. 6, Dusing 1St Rd., Hsinchu Science Park,
Hsinchu, 300096, Taiwan
TEL: 886-3-5635818 Fax: 886-3-5635080

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